

自主封測 品質把控 售後保障

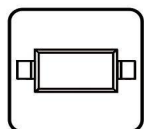
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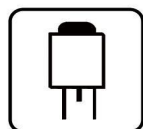
電源管理



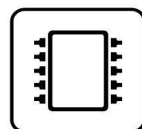
顯示驅動



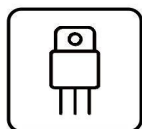
二三極管



LDO穩壓器



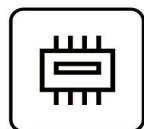
觸摸芯片



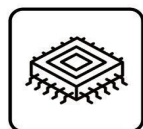
MOS管



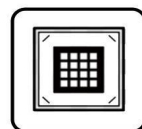
運算放大器



存儲芯片



MCU



串口通信

S8550 2TY 0.4

產品規格說明書

S8550LST1

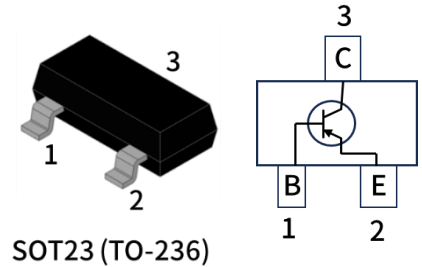
General Purpose Transistors PNP

1. FEATURES

- The material of product compliance with RoHS requirements and Halogen Free.
- High Stability and High Reliability.
- Complementary to S8050 (NPN)

2. Mechanical Data

- SOT-23 Small Outline Plastic Package.
- Tin plated leads, solderable per J-STD-002 and JESD22-B102.
- Marking: 2TY



3. ORDERING INFORMATION

Device	Min Pack	Inner Box	Outer Carton	Reel
S8550LST1	3000	45000	180000	7 inch

4. MAXIMUM RATINGS (Ta = 25°C)

Parameter	Symbol	Limit	Unit
Collector-Emitter Voltage	VCE0	-25	V
Collector-Base Voltage	VCB0	-40	V
Emitter-Base Voltage	VEB0	-5	V
Collector Current	Ic	-500	mA
Collector Power Dissipation	Pc	300	mW

5. THERMAL CHARACTERISTICS

Parameter	Symbol	Limit	Unit
Operation Junction and Storage Temperature Range	TJ, TSTG	-55~150	°C
Thermal Resistance from Junction to Ambient	RθJA	417	°C/W

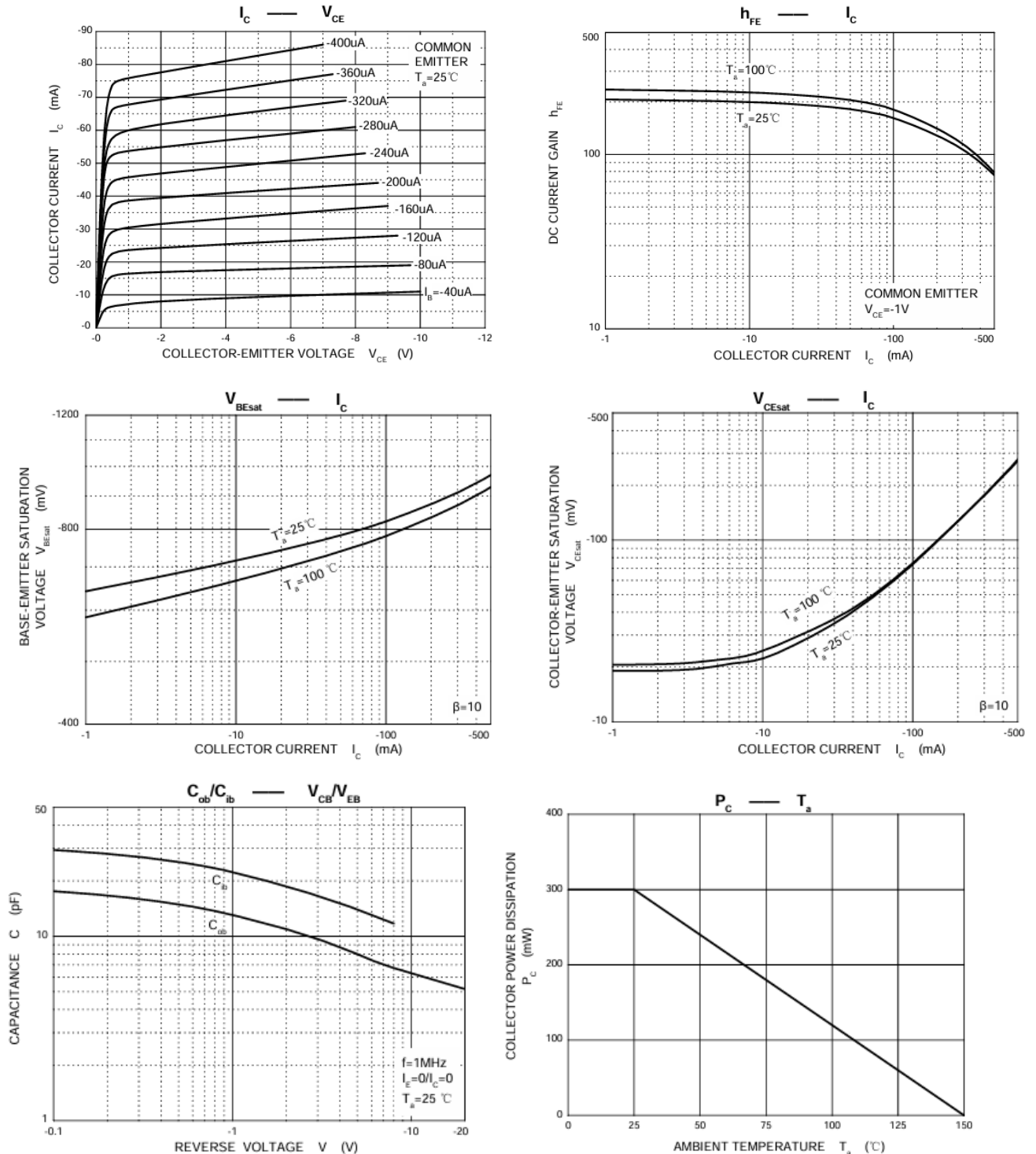
6. ELECTRICAL CHARACTERISTICS (Ta= 25°C unless otherwise specified)

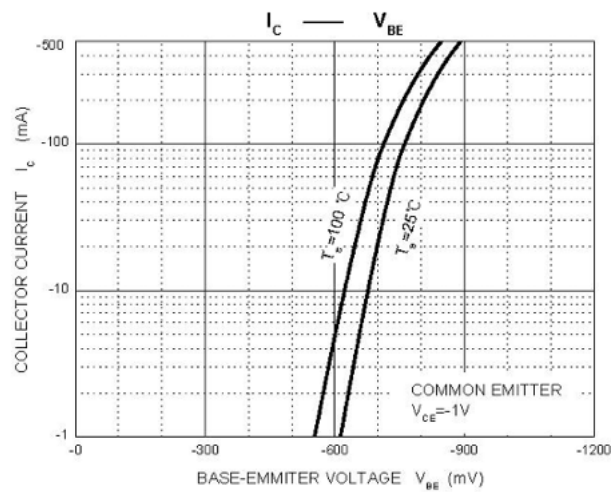
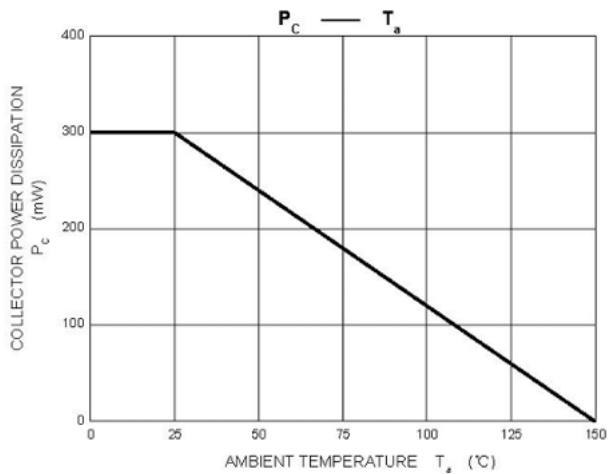
Parameter	Symbol	Condition	Min	Max	Unit
Collector - Emitter Breakdown Voltage	V(BR)CEO	IC = -1 mA, IB = 0	-25		V
Collector - Base Breakdown Voltage	V(BR)CB0	IC = -0.1mA, IE = 0	-40		V
Emitter - Base Breakdown Voltage	V(BR)EB0	IE = -0.1mA, IC = 0	-5		V
Collector Cutoff Current	ICE0	VCE = -20 V, IB = 0		-100	nA
Collector Cutoff Current	ICB0	VCB= -40 V, IE=0		-100	nA
Emitter cut-off current	IEB0	VEB= -3V, IC=0		-100	nA
DC current gain	hFE(1)	IC = -50 mA, VCE = -1 V	120	400	
DC current gain	hFE(2)	IC = -500 mA, VCE = -1 V	50		
Collector-Emitter Saturation Voltage	VCE(sat)	IC = -500 mA, IB = -50 mA		-0.6	V
Base - Emitter Saturation Voltage	VBE(sat)	IC = -500 mA, IB = -50 mA		-1.2	V
Transition frequency	fT	IC = -20mA, VCE= -6V, f = 30MHz	150		MHz

CLASSIFICATION OF $h_{FE}(1)$

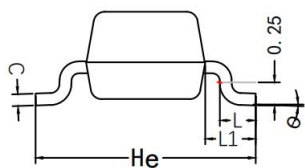
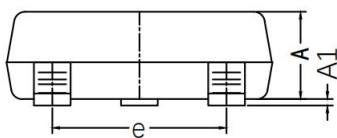
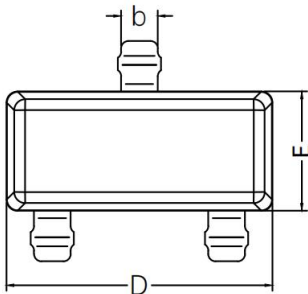
RANK	L	H	J
RANGE	120-200	200-350	300-400

7.ELECTRICAL CHARACTERISTICS CURVES



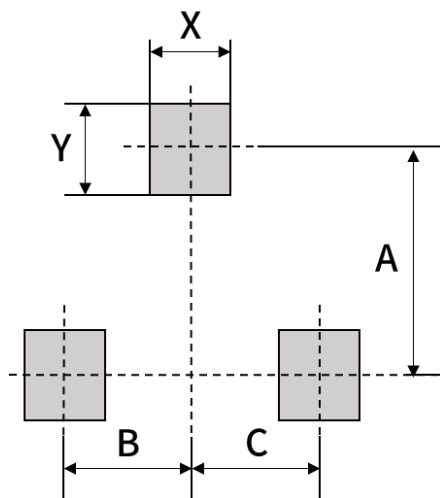


8. OUTLINE AND DIMENSIONS



DIM	MIN	NOR	MAX
A	0.85	0.95	1.05
A1	0.01	0.06	0.10
b	0.36	0.44	0.52
c	0.09	0.13	0.18
D	2.80	2.90	3.10
E	1.20	1.30	1.40
e	1.78	1.90	2.04
L	0.30	0.40	0.50
L1	0.35	0.50	0.65
He	2.10	2.35	2.50
θ	0°	—	10°
All Dimensions in mm			

9. SUGGESTED PAD LAYOUT



SOT23		
DIM	mm	inch
A	2.00	0.079
B	0.95	0.037
C	0.95	0.037
X	0.80	0.031
Y	0.90	0.035